

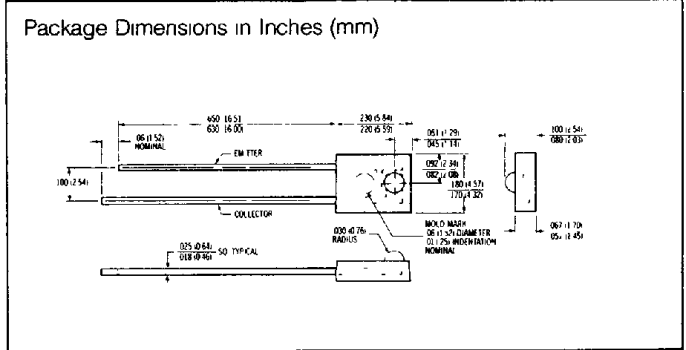
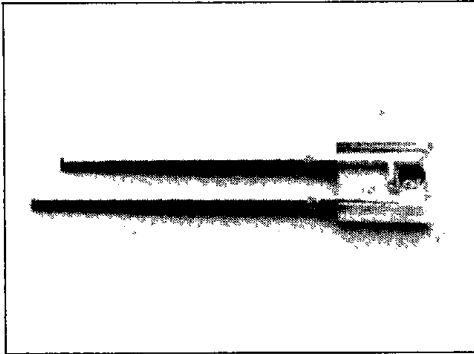
SIEMENS

LPD-80A

PHOTODARLINGTON

T-41-63

Advance Data Sheet



FEATURES

- Silicon NPN Photodarlington
- Miniature Side-Facing Package
- Low Cost
- High Sensitivity
- Matches IRL-80A Infrared Emitter

DESCRIPTION

The LPD-80A is an epitaxial NPN silicon photodarlington. The chip is positioned to accept radiation from the side of the clear miniature package. It efficiently receives infrared radiation from the matching IRL-80A.

Maximum Ratings

Collector Emitter Voltage	V_{CE}	30	V
Emitter Collector Voltage	V_{EC}	5	V
Operating and Storage Temperature	T	-40 to +100	°C
Power Dissipation @ 25°C	P_{tot}	100	mW
Deviation Above 25°C		133	mW/°C

Characteristics (T_{amb} = 25°C)

Photocurrent (Note 1) ($V_{CE} = 5\text{ V}$, $H = 0.5\text{ mW/cm}^2$)	I_{CE}	5	4	mA
Dark Current ($V_{CE} = 10\text{ V}$, $H = 0$)	I_{CEO}		100	nA
Saturation Voltage ($I_C = 250\text{ }\mu\text{A}$ $H = 0.5\text{ mW/cm}^2$)	V_{CEsat}		1.1	V

¹The light source is a tungsten filament bulb used in conjunction with a $950 \pm 30\text{ nm}$ filter. The mechanical axis of the DUT is aligned with the light source.

Specifications are subject to change without notice